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<b>Session Title:</b>	<b>[ThB1] Structural Analysis</b>
<b>Session Date:</b>	<b>July 16 (Thu.), 2026</b>
<b>Session Time:</b>	<b>08:30-10:15</b>
<b>Session Room:</b>	<b>Room B (Baekrok Hall B-2, 1F)</b>
<b>Session Chairs</b>	

<b>[ThB1-1] [Invited]</b>	<b>08:30-09:00</b>
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**MOVPE Growth of AlGaN with Step-and-Terrace Structures on AlN Templates**

Ryota Akaike, Hiroki Yasunaga, Takao Nakamura, and Hideto Miyake, Mie University, Japan

<b>[ThB1-2]</b>	<b>09:00-09:15</b>
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**Atomic Structure of Antiphase Domain Boundaries in III-V Semiconductor Layers Epitaxially Grown on Silicon (100) or Obtained by Direct Wafer Bonding**

Gilles Patriarche<sup>1</sup>, Konstantinos Pantzas<sup>1</sup>, Alexandre Beck<sup>2</sup>, Laurent Pedesseau<sup>2</sup>, Rozenn Gautheron-Bernard<sup>2</sup>, Nathaniel Findling<sup>1</sup>, Ludovic Largeau<sup>1</sup>, Grégoire Beaudoin<sup>1</sup>, Jean-Baptiste Rodriguez<sup>2</sup>, Eric Tournié<sup>3</sup>, Isabelle Sagnes<sup>1</sup>, and Charles Cornet<sup>2</sup>, <sup>1</sup> Centre national de la recherche scientifique, France, <sup>2</sup> Institut National des Sciences Appliquées de Rennes, France, <sup>3</sup> Université de Montpellier, France

<b>[ThB1-3]</b>	<b>09:15-09:30</b>
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**Interplay of Carrier Recombination and Separation in an InGaN MQW LED Investigated by Nano-STEM-EBIC and -STEM-CL**

Niklas Dreyer, Frank Bertram, Gordon Schmidt, Luca Greczmiel, Christoph Berger, Armin Dadgar, André Strittmatter, and Jürgen Christen, Otto-von-Guericke-University Magdeburg, Germany

<b>[ThB1-4]</b>	<b>09:30-09:45</b>
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**Vacancy Properties and Their Clustering in GaN MOVPE Epitaxial Layers and Heterostructures**

Alice Hospodková<sup>1</sup>, Jakub Čížek<sup>2</sup>, František Hájek<sup>1</sup>, Karla Kuldová<sup>1</sup>, Tomáš Hubáček<sup>1</sup>, Jiří Pangrác<sup>1</sup>, Maciej Oskar Liedke<sup>3</sup>, Eric Hirschmann<sup>3</sup>, Maik Butterling<sup>3</sup>, and Andreas Wagner<sup>3</sup>, <sup>1</sup> Institute of Physics of the Czech Academy of Sciences, Czech Republic, <sup>2</sup> Charles University, Czech Republic, <sup>3</sup> Helmholtz-Zentrum Dresden-Rossendorf, Germany

<b>[ThB1-5]</b>	<b>09:45-10:00</b>
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**Revisiting the Stacking Faults in 4H-SiC**

Soon-Ku Hong<sup>1</sup>, Moonkyong Na<sup>2</sup>, Hyundon Jung<sup>3</sup>, and Wook Bahng<sup>2</sup>, <sup>1</sup> Chungnam National University, Korea, <sup>2</sup> Korea Electrotechnology Research Institute, Korea, <sup>3</sup> Horiba STEC Korea, Korea

<b>[ThB1-6]</b>	<b>10:00-10:15</b>
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**Analytical X-Ray Solutions for Thin Film and Wafer Analysis**

Andrey Zameshin<sup>1</sup>, Alexey Pustovarenko<sup>1</sup>, Amardeep Bharti<sup>1</sup>, Choong Ki (Daniel) Lee<sup>2</sup>, and Shuji Kusano<sup>3</sup>, <sup>1</sup> Malvern Panalytical, Netherlands, <sup>2</sup> Spectris Korea Ltd, Korea, <sup>3</sup> Spectris Co. Ltd, Japan